

**SiC**

Silicon Carbide Diode

**5<sup>th</sup> Generation thinQ!<sup>TM</sup>**

650V SiC Schottky Diode

**IDW16G65C5**

**Final Datasheet**

Rev. 2.2, 2013-01-15

**Power Management & Multimarket**

## 5<sup>th</sup> Generation thinQ!<sup>TM</sup> SiC Schottky Diode

### 1 Description

ThinQ!<sup>TM</sup> Generation 5 represents Infineon leading edge technology for the SiC Schottky Barrier diodes. Thanks to the more compact design and thin-wafer technology, the new family of products shows improved efficiency over all load conditions, resulting from both the improved thermal characteristics and a lower figure of merit ( $Q_c \times V_f$ ).

The new thinQ!<sup>TM</sup> Generation 5 has been designed to complement our 650V CoolMOS<sup>TM</sup> families: this ensures meeting the most stringent application requirements in this voltage range.

#### Features

- Revolutionary semiconductor material - Silicon Carbide
- Benchmark switching behavior
- No reverse recovery/ No forward recovery
- Temperature independent switching behavior
- High surge current capability
- Pb-free lead plating; RoHS compliant
- Qualified according to JEDEC<sup>1)</sup> for target applications
- Breakdown voltage tested at 35 mA<sup>2)</sup>
- Optimized for high temperature operation

#### Benefits

- System efficiency improvement over Si diodes
- System cost / size savings due to reduced cooling requirements
- Enabling higher frequency / increased power density solutions
- Higher system reliability due to lower operating temperatures
- Reduced EMI

#### Applications

- Switch mode power supply
- Power factor correction
- Solar inverter
- Uninterruptible power supply

**Table 1 Key Performance Parameters**

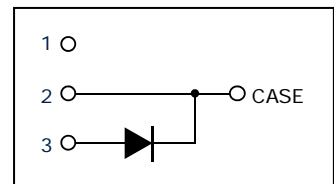
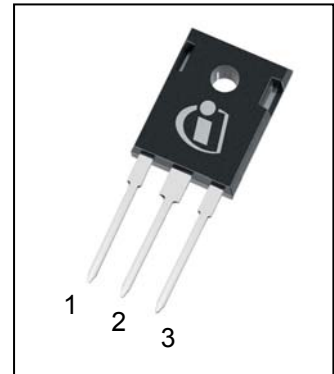
| Parameter                 | Value | Unit    |
|---------------------------|-------|---------|
| $V_{DC}$                  | 650   | V       |
| $Q_C; V_R=400V$           | 23    | nC      |
| $E_C; V_R=400V$           | 5.3   | $\mu J$ |
| $I_F @ T_C < 120^\circ C$ | 16    | A       |

**Table 2 Pin Definition**

| Pin 1 | Pin 2 | Pin 3 |
|-------|-------|-------|
| n.c.  | C     | A     |

| Type / ordering Code | Package    | Marking | Related links  |
|----------------------|------------|---------|--|
| IDW16G65C5           | PG-TO247-3 | D1665C5 | <a href="http://www.infineon.com/sic">www.infineon.com/sic</a> |

### IDW16G65C5



1) J-STD20 and JESD22

2) All devices tested under avalanche conditions for a time period of 10ms

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## 2 Maximum ratings

**Table 3** Maximum ratings

| Parameter   | Symbol         | Values |      |      | Unit             | Note/Test Condition                                    |
|---|----------------|--------|------|------|------------------|--|
|   |                | Min.   | Typ. | Max. |                  |  |
| Continuous forward current                          | $I_F$          | –      | –    | 16   | A                | $T_C < 120^\circ\text{C}$ , $D=1$                      |
| Surge non-repetitive forward current, sine halfwave | $I_{F,SM}$     | –      | –    | 95   |                  | $T_C = 25^\circ\text{C}$ , $t_p=10\text{ ms}$          |
|   |                | –      | –    | 74   |                  | $T_C = 150^\circ\text{C}$ , $t_p=10\text{ ms}$         |
| Non-repetitive peak forward current                 | $I_{F,max}$    | –      | –    | 637  |                  | $T_C = 25^\circ\text{C}$ , $t_p=10\text{ }\mu\text{s}$ |
| $i^2t$ value  | $\int i^2 dt$  | –      | –    | 45   | A <sup>2</sup> s | $T_C = 25^\circ\text{C}$ , $t_p=10\text{ ms}$          |
|   |                | –      | –    | 28   |                  | $T_C = 150^\circ\text{C}$ , $t_p=10\text{ ms}$         |
| Repetitive peak reverse voltage                     | $V_{RRM}$      | –      | –    | 650  | V                |  |
| Diode dv/dt ruggedness                              | $dv/dt$        | –      | –    | 100  | V/ns             | $V_R=0..480\text{ V}$                                  |
| Power dissipation                                   | $P_{tot}$      | –      | –    | 94   | W                | $T_C = 25^\circ\text{C}$                               |
| Operating and storage temperature                   | $T_j; T_{stg}$ | -55    | –    | 175  | °C               |  |
| Mounting torque                                     |                | –      | 50   | 70   | Ncm              | M3 and M4 screws                                       |

## 3 Thermal characteristics

**Table 4** Thermal characteristics TO-247-3

| Parameter  | Symbol     | Values |      |      | Unit | Note/Test Condition                  |
|--|------------|--------|------|------|------|--------------------------------------|
|  |            | Min.   | Typ. | Max. |      |                                      |
| Thermal resistance, junction-case                          | $R_{thJC}$ | –      | 1.2  | 1.6  | K/W  | leaded                               |
| Thermal resistance, junction-ambient                       | $R_{thJA}$ | –      | –    | 62   |      |                                      |
| Soldering temperature, wavesoldering only allowed at leads | $T_{sold}$ | –      | –    | 260  | °C   | 1.6mm (0.063 in.) from case for 10 s |

## 4 Electrical characteristics

**Table 5 Static characteristics**

| Parameter             | Symbol   | Values |      |      | Unit          | Note/Test Condition                            |
|-----------------------|----------|--------|------|------|---------------|--|
|                       |          | Min.   | Typ. | Max. |               |  |
| DC blocking voltage   | $V_{DC}$ | 650    | –    | –    | V             | $I_R = 0.2 \text{ mA}, T_j = 25^\circ\text{C}$ |
| Diode forward voltage | $V_F$    | –      | 1.5  | 1.7  |               | $I_F = 16 \text{ A}, T_j = 25^\circ\text{C}$   |
|                       |          | –      | 1.8  | 2.1  |               | $I_F = 16 \text{ A}, T_j = 150^\circ\text{C}$  |
| Reverse current       | $I_R$    | –      | 0.8  | 200  | $\mu\text{A}$ | $V_R = 650 \text{ V}, T_j = 25^\circ\text{C}$  |
|                       |          | –      | 0.2  | 71   |               | $V_R = 600 \text{ V}, T_j = 25^\circ\text{C}$  |
|                       |          | –      | 3.2  | 1400 |               | $V_R = 650 \text{ V}, T_j = 150^\circ\text{C}$ |

**Table 6 AC characteristics**

| Parameter               | Symbol | Values |      |      | Unit | Note/Test Condition  |
|-------------------------|--------|--------|------|------|------|--|
|                         |        | Min.   | Typ. | Max. |      |  |
| Total capacitive charge | $Q_c$  | –      | 23   | –    | nC   | $V_R = 400 \text{ V}, di/dt = 200 \text{ A}/\mu\text{s}, I_F \leq I_{F,MAX}, T_j = 150^\circ\text{C}.$ |
| Total Capacitance       | C      | –      | 470  | –    | pF   | $V_R = 1 \text{ V}, f = 1 \text{ MHz}$   |
|                         |        | –      | 61   | –    |      | $V_R = 300 \text{ V}, f = 1 \text{ MHz}$   |
|                         |        | –      | 60   | –    |      | $V_R = 600 \text{ V}, f = 1 \text{ MHz}$   |

## 5 Electrical characteristics diagrams

Table 7

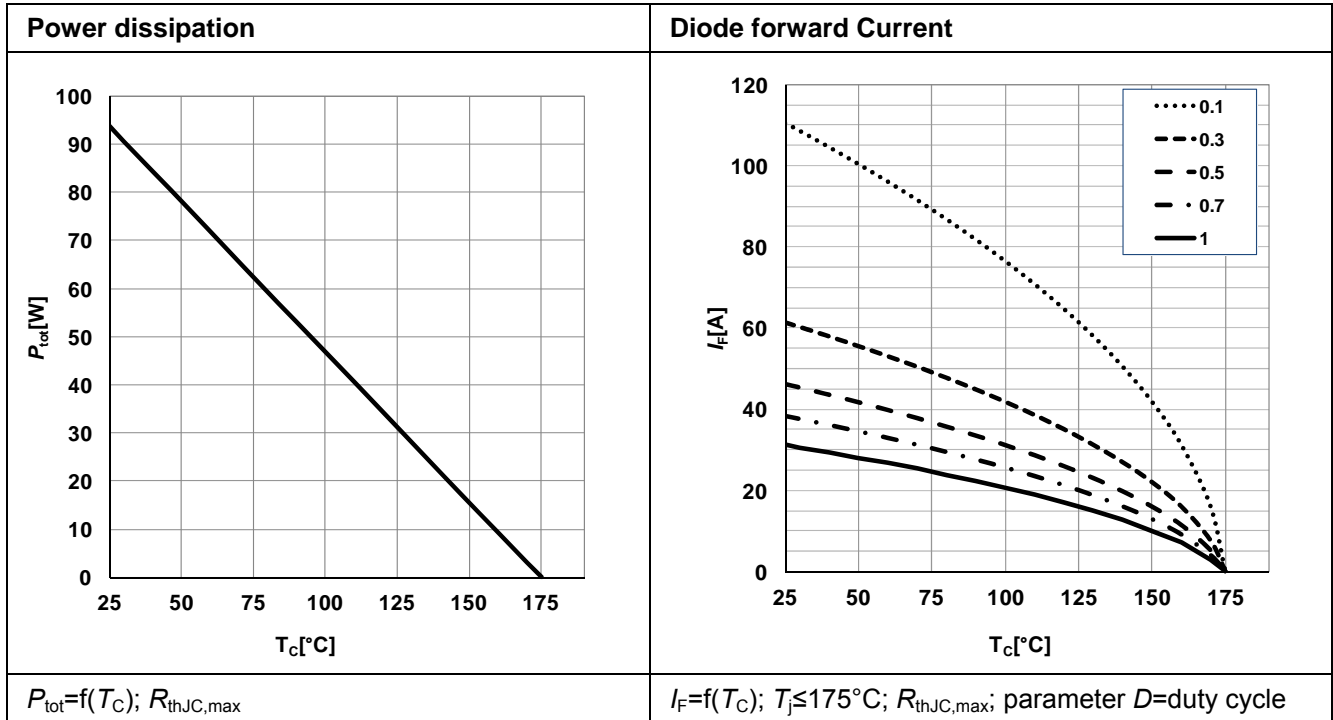


Table 8

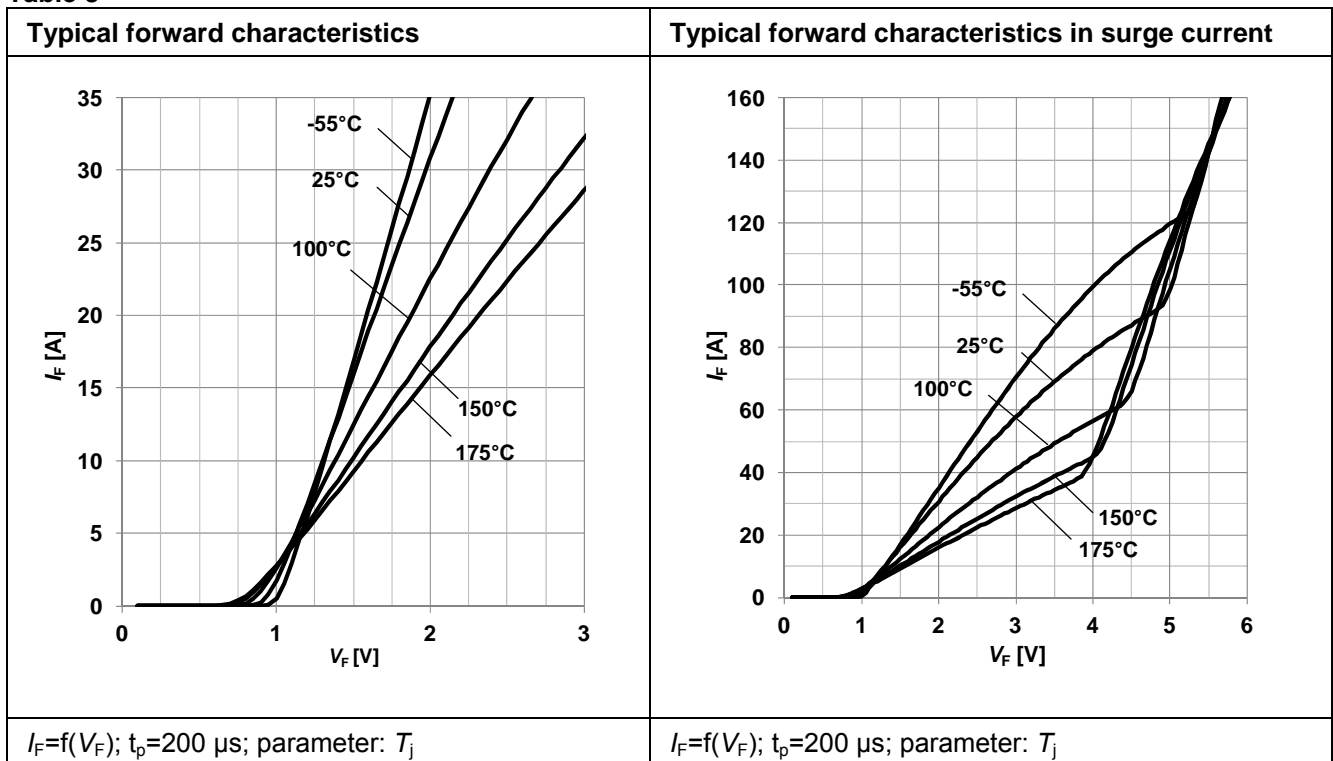


Table 9

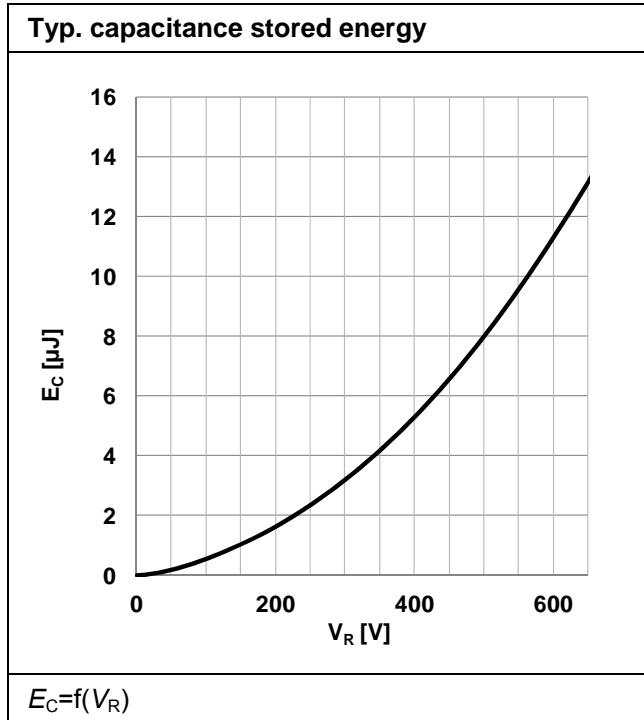
| Typ. capacitance charge vs. current slope <sup>1)</sup>                        | Typ. reverse current vs. reverse voltage |
|--|--|
|  |  |
| $Q_C=f(di_F/dt); T_j=150^{\circ}\text{C}; V_R=400\text{ V}; I_F\leq I_{F,max}$ | $I_R=f(V_R); \text{parameter: } T_j;$    |

1) Only capacitive charge, guaranteed by design.

Table 10

| Max. transient thermal impedance                | Typ. capacitance vs. reverse voltage               |
|---|--|
|   |  |
| $Z_{th,jc}=f(t_p); \text{parameter: } D=t_p/T;$ | $C=f(V_R); T_j=25^{\circ}\text{C}; f=1\text{ MHz}$ |

Table 11



## 6 Simplified Forward Characteristics Model

Table 12

| Equivalent forward current curve | Mathematical Equation  |
|----------------------------------|--|
|                                  | $V_F = V_{TH} + R_{DIFF} \cdot I_F$ $V_{TH}(T_j) = -0.001 \cdot T_j + 1.04 \text{ [V]}$ $R_{DIFF}(T_j) = 8 \cdot 10^{-7} \cdot T_j^2 + 8 \cdot 10^{-5} \cdot T_j + 0.029 \text{ [\Omega]}$ |
| $V_F = f(I_F)$                   | $T_j$ in °C; $-55^\circ\text{C} < T_j < 175^\circ\text{C}$ ; $I_F < 32 \text{ A}$  |



7 Package outlines

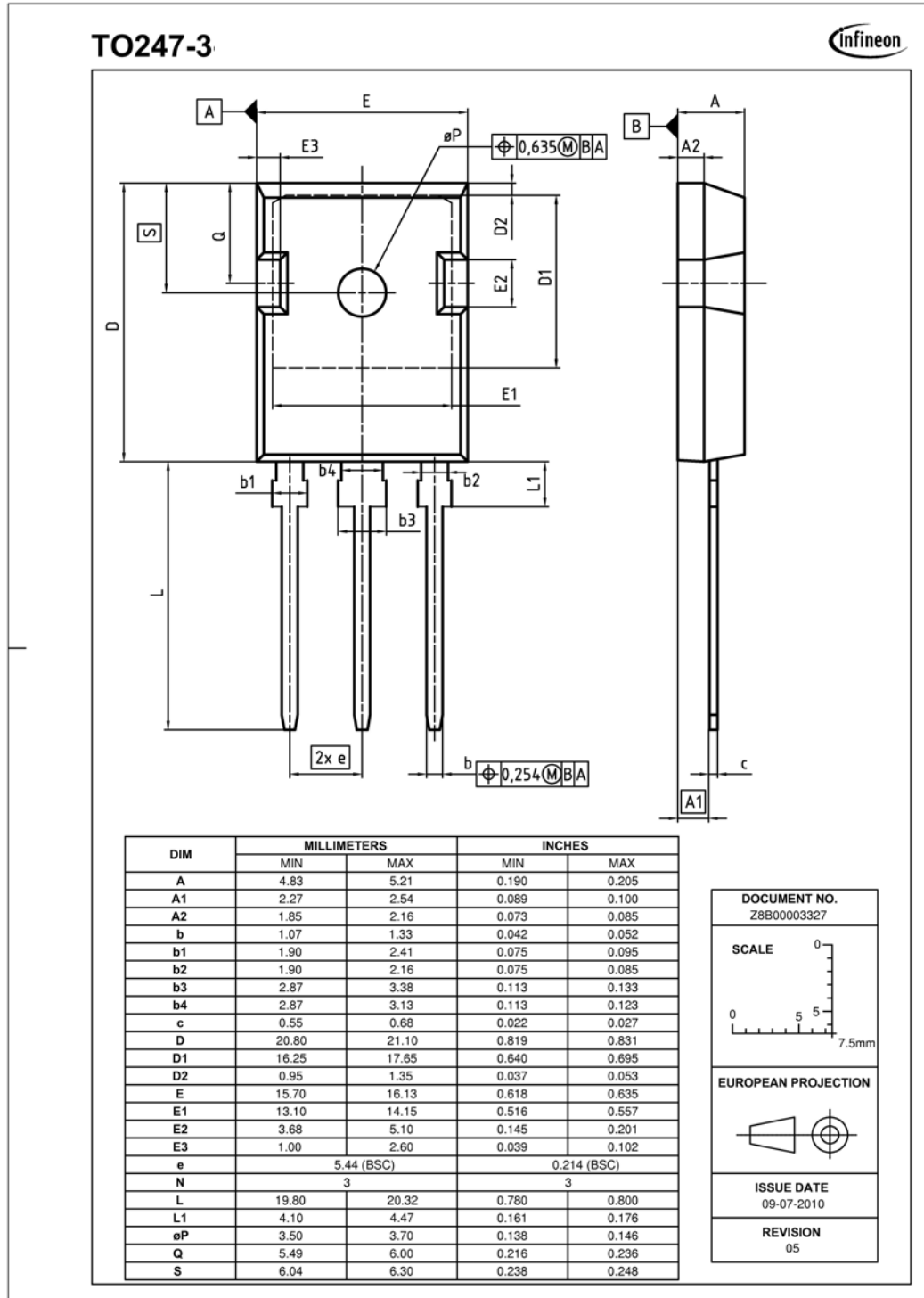


Figure 1 Outlines TO-247, dimensions in mm/inches

## 8 Revision History

### 5<sup>th</sup> Generation thinQ!™ SiC Schottky Diode

#### Revision History: 2013-01-15, Rev. 2.2

##### Previous Revision:

| Revision | Subjects (major changes since last version)                                    |
|----------|--|
| 2.0      | Release of the final datasheet.  |
| 2.1      | Reverse current values, maximum diode forward voltage.                         |
| 2.2      | Reverse current values, tested avalanche current, simplified calculation model |

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